

**2N5637**

## SILICON BIPOLAR NPN POWER TRANSISTOR 20 W, up to 400 MHz

The silicon bipolar n-p-n transistor is designed for UHF communications transmitters.

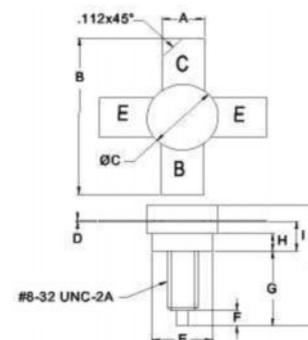
Features (At 400 MHz):

- Output Power: 20 W
- Power Gain: 6.1 dB Typ
- Efficiency: 60% Min

### Absolute Maximum Ratings

Parameters	Sym	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	35	$V_{DC}$
Collector–Base Voltage	$V_{CBO}$	60	$V_{DC}$
Emitter–Base Voltage	$V_{EBO}$	4	$V_{DC}$
Collector Current	$I_C$	3	$A_{DC}$
Operation Junction Temperature	$T_J$	-65 ÷ +200	°C
Storage Temperature Range	$T_{STG}$	-65 ÷ +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5.8	°C/W
Total Power Dissipation, $T_C=25^\circ C$	$P_D$	30	W

### PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

### Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage ( $I_C = 200 \text{ mA}$ , $I_B = 0 \text{ A}$ )	$V_{(BR)CEO}$	35	—	—	$V_{DC}$
Collector–Emitter Breakdown Voltage ( $I_C = 200 \text{ mA}$ , $V_{BE} = 0 \text{ V}$ )	$V_{(BR)CER}$	60	—	—	$V_{DC}$
Emitter–Base Breakdown Voltage ( $I_E = 10 \text{ mA}$ , $I_C = 0 \text{ A}$ )	$V_{(BR)EBO}$	4	—	—	$V_{DC}$
Collector– Base Leakage Current ( $V_{CB} = 30 \text{ V}$ , $I_E = 0 \text{ A}$ )	$I_{CBO}$	—	—	0.1	$\text{mA}_{DC}$
DC Current Gain ( $V_{CE} = 5 \text{ V}$ , $I_C = 500 \text{ mA}$ )	$h_{FE}$	5	—	100	
Output Capacitance ( $V_{CB} = 30 \text{ V}$ , $I_C = 0 \text{ A}$ , $f = 1 \text{ MHz}$ )	$C_{OB}$	—	—	30	pF
Power Gain ( $V_{CE} = 28 \text{ V}$ , $f = 400 \text{ MHz}$ , $P_{OUT} = 20 \text{ W}$ )	$G_p$	—	6.1	—	dB
Drain Efficiency ( $V_{CE} = 28 \text{ V}$ , $f = 400 \text{ MHz}$ , $P_{OUT} = 20 \text{ W}$ )	$\eta$	60	—	—	%

### ZAO 'Syntez Microelectronics'

119V Leninsky Prospekt, Voronezh 394007, Russia • Tel +7-4732-379-101 Fax +7-4732-266-057

[exim@syntezmicro.ru](mailto:exim@syntezmicro.ru)

[www.syntezmicro.ru](http://www.syntezmicro.ru)

Specification is subject to change without notice